

ETCHING OF SILICON CARBIDE FILMS FROM REACTOR PARTS

ABSTRACT

5 The present invention relates to a method for etching a silicon carbide
accretion from one or more workpieces of a reaction chamber for the deposition of
silicon carbide layers on a substrate. The method comprises the steps of: (I) providing
a silicon carbide accretion on one or more workpieces of a reaction chamber of a
reactor for deposition of silicon carbide; (II) executing at least one cycle of an etching
10 process. The present invention further relates to a reactor adapted to execute said
method.

(fig.1)